Welcome to E-XFL.COM

Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e500
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	833MHz
Co-Processors/DSP	-
RAM Controllers	DDR, SDRAM
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (1), 10/100/1000Mbps (2)
SATA	-
USB	-
Voltage - I/O	2.5V, 3.3V
Operating Temperature	0°C ~ 105°C (TA)
Security Features	-
Package / Case	784-BBGA, FCBGA
Supplier Device Package	783-FCPBGA (29x29)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8540vt833lc

2.1.2 Power Sequencing

The MPC8540 requires its power rails to be applied in a specific sequence in order to ensure proper device operation. These requirements are as follows for power up:

1. V_{DD}, AV_{DD}
2. GV_{DD}, LV_{DD}, OV_{DD} (I/O supplies)

Items on the same line have no ordering requirement with respect to one another. Items on separate lines must be ordered sequentially such that voltage rails on a previous step must reach 90 percent of their value before the voltage rails on the current step reach 10 percent of theirs.

NOTE

If the items on line 2 must precede items on line 1, please ensure that the delay will not exceed 500 ms and the power sequence is not done greater than once per day in production environment.

NOTE

From a system standpoint, if the I/O power supplies ramp prior to the V_{DD} core supply, the I/Os on the MPC8540 may drive a logic one or zero during power-up.

2.1.3 Recommended Operating Conditions

Table 2 provides the recommended operating conditions for the MPC8540. Note that the values in Table 2 are the recommended and tested operating conditions. Proper device operation outside of these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Characteristic	Symbol	Recommended Value	Unit
Core supply voltage For devices rated at 667 and 833 MHz For devices rated at 1 GHz	V_{DD}	 1.2 V ± 60 mV 1.3 V ± 50 mV	V
PLL supply voltage For devices rated at 667 and 833 MHz For devices rated at 1 GHz	AV_{DD}	 1.2 V ± 60 mV 1.3 V ± 50 mV	V
DDR DRAM I/O voltage	GV_{DD}	2.5 V ± 125 mV	V
Three-speed Ethernet I/O voltage	LV_{DD}	3.3 V ± 165 mV 2.5 V ± 125 mV	V
PCI/PCI-X, local bus, RapidIO, 10/100 Ethernet, MII management, DUART, system control and power management, I^2C, and JTAG I/O voltage	OV_{DD}	3.3 V ± 165 mV	V

4.3 RapidIO Transmit Clock Input Timing

Table 9 provides the RapidIO transmit clock input (RIO_TX_CLK_IN) AC timing specifications for the MPC8540.

Table 9. RIO_TX_CLK_IN AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
RIO_TX_CLK_IN frequency	f_{RCLK}	125	—	—	MHz	
RIO_TX_CLK_IN cycle time	t_{RCLK}	—	—	8	ns	
RIO_TX_CLK_IN duty cycle	t_{RCLKH}/t_{RCLK}	48	—	52	%	1

Notes:

1. Requires ±100 ppm long term frequency stability. Timing is guaranteed by design and characterization.

4.4 Real Time Clock Timing

Table 10 provides the real time clock (RTC) AC timing specifications for the MPC8540.

Table 10. RTC AC Timing Specifications

Parameter/Condition	Symbol	Min	Typical	Max	Unit	Notes
RTC clock high time	t_{RTCH}	2 x t_{CCB_CLK}	—	—	ns	
RTC clock low time	t_{RTCL}	2 x t_{CCB_CLK}	—	—	ns	

5 RESET Initialization

This section describes the AC electrical specifications for the RESET initialization timing requirements of the MPC8540. Table 7 provides the RESET initialization AC timing specifications for the MPC8540.

Table 11. RESET Initialization Timing Specifications

Parameter/Condition	Min	Max	Unit	Notes
Required assertion time of $\overline{\text{HRESET}}$	100	—	μs	
Minimum assertion time for $\overline{\text{SRESET}}$	512	—	SYSCLKs	1
PLL input setup time with stable SYSCLK before $\overline{\text{HRESET}}$ negation	100	—	μs	
Input setup time for POR configs (other than PLL config) with respect to negation of $\overline{\text{HRESET}}$	4	—	SYSCLKs	1
Input hold time for POR configs (including PLL config) with respect to negation of $\overline{\text{HRESET}}$	2	—	SYSCLKs	1

Table 13. DDR SDRAM DC Electrical Characteristics (continued)

Parameter/Condition	Symbol	Min	Max	Unit	Notes
MV_{REF} input leakage current	I_{VREF}	—	100	μA	

Notes:

1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MV_{REF} is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MV_{REF} may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MV_{REF}. This rail should track variations in the DC level of MV_{REF}.
4. V_{IH} can tolerate an overshoot of 1.2V over GV_{DD} for a pulse width of ≤3 ns, and the pulse width cannot be greater than t_{MCK}. V_{IL} can tolerate an undershoot of 1.2V below GND for a pulse width of ≤3 ns, and the pulse width cannot be greater than t_{MCK}.
5. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

Table 14 provides the DDR capacitance.

Table 14. DDR SDRAM Capacitance

Parameter/Condition	Symbol	Min	Max	Unit	Notes
Input/output capacitance: DQ, DQS, MSYNC_IN	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:

1. This parameter is sampled. GV_{DD} = 2.5 V ± 0.125 V, f = 1 MHz, T_A = 25°C, V_{OUT} = GV_{DD}/2, V_{OUT} (peak to peak) = 0.2 V.

6.2 DDR SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR SDRAM interface.

6.2.1 DDR SDRAM Input AC Timing Specifications

Table 15 provides the input AC timing specifications for the DDR SDRAM interface.

Table 15. DDR SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
AC input low voltage	V_{IL}	—	MV_{REF} – 0.31	V	
AC input high voltage	V_{IH}	MV_{REF} + 0.31	GV_{DD} + 0.3	V	
MDQS—MDQ/MECC input skew per byte For DDR = 333 MHz For DDR ≤ 266 MHz	t_{DISKEW}	 -750 -1125	 750 1125	ps	1, 2

Note:

1. Maximum possible skew between a data strobe (MDQS[n]) and any corresponding bit of data (MDQ[8n + {0...7}] if 0 ≤ n ≤ 7) or ECC (MECC[{0...7}] if n=8).
2. For timing budget analysis, the MPC8540 consumes ±550 ps of the total budget.

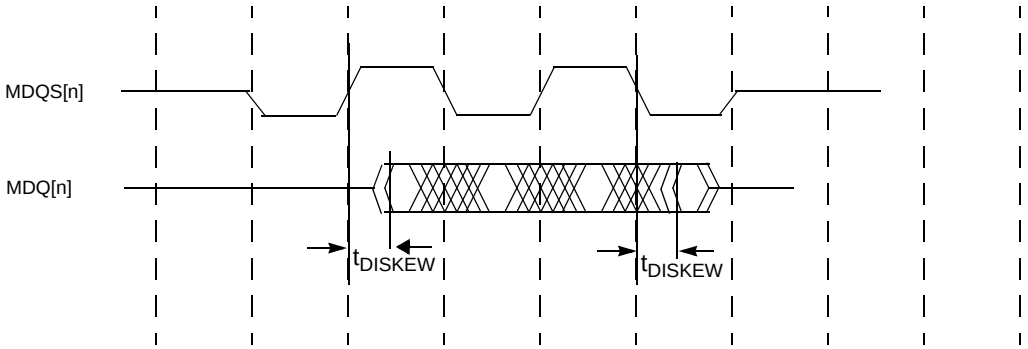

Figure 4. DDR SDRAM Interface Input Timing

6.2.2 DDR SDRAM Output AC Timing Specifications

For chip selects $\overline{\text{MCS1}}$ and $\overline{\text{MCS2}}$, there will always be at least 200 DDR memory clocks coming out of self-refresh after an $\overline{\text{HRESET}}$ before a precharge occurs. This will not necessarily be the case for chip selects $\overline{\text{MCS0}}$ and $\overline{\text{MCS3}}$.

6.2.2.1 DLL Enabled Mode

Table 16 and Table 17 provide the output AC timing specifications and measurement conditions for the DDR SDRAM interface with the DDR DLL enabled.

Table 16. DDR SDRAM Output AC Timing Specifications–DLL Mode

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol [1]	Min	Max	Unit	Notes
MCK[n] cycle time, (MCK[n]/$\overline{\text{MCK}}$[n] crossing)	t_{MCK}	6	10	ns	2
On chip Clock Skew	$t_{MCKSKEW}$	—	150	ps	3, 8
MCK[n] duty cycle	t_{MCKH}/t_{MCK}	45	55	%	8
ADDR/CMD output valid	t_{DDKHOV}	—	3	ns	4, 9
ADDR/CMD output invalid	t_{DDKHOX}	1	—	ns	4, 9
Write CMD to first MDQS capture edge	t_{DDSHMH}	t_{MCK} + 1.5	t_{MCK} + 4.0	ns	5
MDQ/MECC/MDM output setup with respect to MDQS 333 MHz 266 MHz 200 MHz	t_{DDKHDS}, t_{DDKLDS}	 900 1100 1200	—	ps	6, 9
MDQ/MECC/MDM output hold with respect to MDQS 333 MHz 266 MHz 200 MHz	t_{DDKHDX}, t_{DDKLDX}	 900 1100 1200	—	ps	6, 9
MDQS preamble start	t_{DDSHMP}	0.75 × t_{MCK} + 1.5	0.75 × t_{MCK} + 4.0	ns	7, 8

Table 16. DDR SDRAM Output AC Timing Specifications–DLL Mode (continued)

At recommended operating conditions with GV_{DD} of 2.5 V ± 5%.

Parameter	Symbol [1]	Min	Max	Unit	Notes
MDQS epilogue end	t_{DDSHME}	1.5	4.0	ns	7, 8

Notes:

1.The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. Output hold time can be read as DDR timing (DD) from the rising or falling edge of the reference clock (KH or KL) until the output went invalid (OX or DX). For example, t_{DDKHOV} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes from the high (H) state until outputs (O) are valid (V) or output valid time. Also, t_{DDKLDX} symbolizes DDR timing (DD) for the time t_{MCK} memory clock reference (K) goes low (L) until data outputs (D) are invalid (X) or data output hold time.

2.All MCK/$\overline{\text{MCK}}$ referenced measurements are made from the crossing of the two signals ±0.1 V.

3.Maximum possible clock skew between a clock MCK[n] and its relative inverse clock $\overline{\text{MCK}}$[n], or between a clock MCK[n] and a relative clock MCK[m] or MSYNC_OUT. Skew measured between complementary signals at $GV_{DD}/2$.

4.ADDR/CMD includes all DDR SDRAM output signals except MCK/$\overline{\text{MCK}}$ and MDQ/MECC/MDM/MDQS.

5.Note that t_{DDSHMH} follows the symbol conventions described in note 1. For example, t_{DDSHMH} describes the DDR timing (DD) from the rising edge of the MSYNC_IN clock (SH) until the MDQS signal is valid (MH). t_{DDSHMH} can be modified through control of the DQSS override bits in the TIMING_CFG_2 register. These controls allow the relationship between the synchronous clock control timing and the source-synchronous DQS domain to be modified by the user. For best turnaround times, these may need to be set to delay t_{DDSHMH} an additional $0.25t_{MCK}$. This will also affect t_{DDSHMP} and t_{DDSHME} accordingly. See the *MPC8540 PowerQUICC III Integrated Host Processor Reference Manual* for a description and understanding of the timing modifications enabled by use of these bits.

6.Determined by maximum possible skew between a data strobe (MDQS) and any corresponding bit of data (MDQ), ECC (MECC), or data mask (MDM). The data strobe should be centered inside of the data eye at the pins of the MPC8540.

7.All outputs are referenced to the rising edge of MSYNC_IN (S) at the pins of the MPC8540. Note that t_{DDSHMP} follows the symbol conventions described in note 1. For example, t_{DDSHMP} describes the DDR timing (DD) from the rising edge of the MSYNC_IN clock (SH) for the duration of the MDQS signal precharge period (MP).

8.Guaranteed by design.

9.Guaranteed by characterization.

Figure 5 provides the AC test load for the DDR bus.

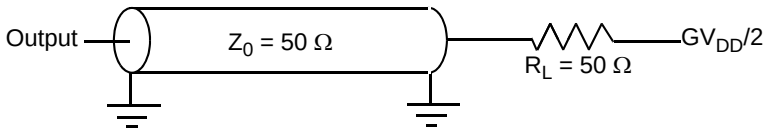

Figure 5. DDR AC Test Load

Table 17. DDR SDRAM Measurement Conditions

Symbol	DDR	Unit	Notes
V_{TH}	MV_{REF} ± 0.31 V	V	1
V_{OUT}	0.5 × GV_{DD}	V	2

Notes:

1.Data input threshold measurement point.

2.Data output measurement point.

Figure 16 shows the MII receive AC timing diagram.

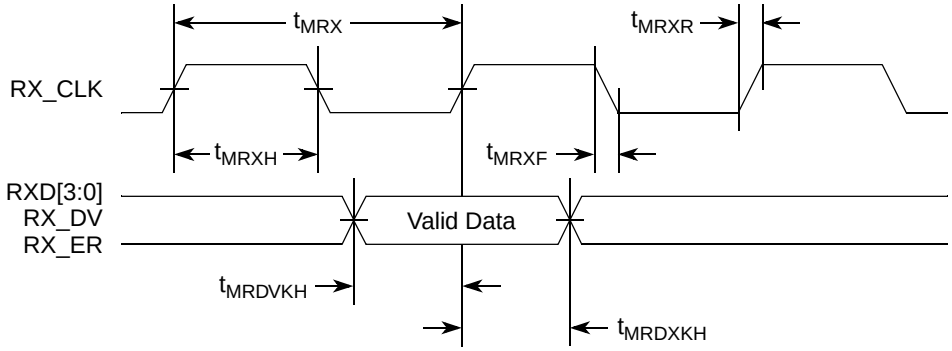

Figure 16. MII Receive AC Timing Diagram

8.4 Ethernet Management Interface Electrical Characteristics

The electrical characteristics specified here apply to MII management interface signals MDIO (management data input/output) and MDC (management data clock). The electrical characteristics for GMII, RGMII, TBI and RTBI are specified in Section 8.1, "Three-Speed Ethernet Controller (TSEC) (10/100/1Gb Mbps)—GMII/MII/TBI/RGMII/RTBI Electrical Characteristics."

8.4.1 MII Management DC Electrical Characteristics

The MDC and MDIO are defined to operate at a supply voltage of 3.3 V. The DC electrical characteristics for MDIO and MDC are provided in Table 33.

Table 33. MII Management DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
Supply voltage (3.3 V)	OV_{DD}	3.13	3.47	V
Output high voltage (OV_{DD} = Min, I_{OH} = –1.0 mA)	V_{OH}	2.10	OV_{DD} + 0.3	V
Output low voltage (OV_{DD} = Min, I_{OL} = 1.0 mA)	V_{OL}	GND	0.50	V
Input high voltage	V_{IH}	1.70	—	V
Input low voltage	V_{IL}	—	0.90	V
Input high current (OV_{DD} = Max, V_{IN} [1] = 2.1 V)	I_{IH}	—	40	μA
Input low current (OV_{DD} = Max, V_{IN} = 0.5 V)	I_{IL}	–600	—	μA

Note:

1.Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

9 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8540.

9.1 Local Bus DC Electrical Characteristics

Table 35 provides the DC electrical characteristics for the local bus interface.

Table 35. Local Bus DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current (V_{IN} [1] = 0 V or V_{IN} = V_{DD})	I_{IN}	—	±5	μA
High-level output voltage (OV_{DD} = min, I_{OH} = –2 mA)	V_{OH}	OV_{DD} - 0.2	—	V
Low-level output voltage (OV_{DD} = min, I_{OL} = 2 mA)	V_{OL}	—	0.2	V

Note:

1.Note that the symbol V_{IN}, in this case, represents the OV_{IN} symbol referenced in Table 1 and Table 2.

9.2 Local Bus AC Electrical Specifications

Table 36 describes the general timing parameters of the local bus interface of the MPC8540 with the DLL enabled.

Table 36. Local Bus General Timing Parameters - DLL Enabled

Parameter	POR Configuration	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time		t_{LBK}	6.0	—	ns	2
LCLK[n] skew to LCLK[m] or LSYNC_OUT		$t_{LBKSKEW}$	—	150	ps	3, 9
Input setup to local bus clock (except LUPWAIT)		$t_{LBIVKH1}$	1.8	—	ns	4, 5, 8
LUPWAIT input setup to local bus clock		$t_{LBIVKH2}$	1.7	—	ns	4, 5
Input hold from local bus clock (except LUPWAIT)		$t_{LBIXKH1}$	0.5	—	ns	4, 5, 8
LUPWAIT input hold from local bus clock		$t_{LBIXKH2}$	1.0	—	ns	4, 5
LALE output transition to LAD/LDP output transition (LATCH hold time)		t_{LBOTOT}	1.5	—	ns	6

Table 37 describes the general timing parameters of the local bus interface of the MPC8540 with the DLL bypassed.

Table 37. Local Bus General Timing Parameters—DLL Bypassed

Parameter	POR Configuration	Symbol [1]	Min	Max	Unit	Notes
Local bus cycle time		t_{LBK}	6.0	—	ns	2
Internal launch/capture clock to LCLK delay		t_{LBKHKT}	2.3	3.9	ns	8
LCLK[n] skew to LCLK[m] or LSYNC_OUT		$t_{LBKSKEW}$	—	150	ps	3, 9
Input setup to local bus clock (except LUPWAIT)		$t_{LBIVKH1}$	5.7	—	ns	4, 5
LUPWAIT input setup to local bus clock		$t_{LBIVKH2}$	5.6	—	ns	4, 5
Input hold from local bus clock (except LUPWAIT)		$t_{LBIXKH1}$	-1.8	—	ns	4, 5
LUPWAIT input hold from local bus clock		$t_{LBIXKH2}$	-1.3	—	ns	4, 5
LALE output transition to LAD/LDP output transition (LATCH hold time)		t_{LBOTOT}	1.5	—	ns	6
Local bus clock to output valid (except LAD/LDP and LALE)	TSEC2_TXD[6:5] = 00	$t_{LBKLOV1}$	—	-0.3	ns	4
	TSEC2_TXD[6:5] = 11 (default)			1.2		
Local bus clock to data valid for LAD/LDP	TSEC2_TXD[6:5] = 00	$t_{LBKLOV2}$	—	-0.1	ns	4
	TSEC2_TXD[6:5] = 11 (default)			1.4		
Local bus clock to address valid for LAD	TSEC2_TXD[6:5] = 00	$t_{LBKLOV3}$	—	0	ns	4
	TSEC2_TXD[6:5] = 11 (default)			1.5		
Local bus clock to LALE assertion		$t_{LBKHOV4}$	—	0	ns	4
Output hold from local bus clock (except LAD/LDP and LALE)	TSEC2_TXD[6:5] = 00	$t_{LBKLOX1}$	-3.2	—	ns	4
	TSEC2_TXD[6:5] = 11 (default)		-2.3			
Output hold from local bus clock for LAD/LDP	TSEC2_TXD[6:5] = 00	$t_{LBKLOX2}$	-3.2	—	ns	4
	TSEC2_TXD[6:5] = 11 (default)		-2.3			
Local bus clock to output high Impedance (except LAD/LDP and LALE)	TSEC2_TXD[6:5] = 00	$t_{LBKLOZ1}$	—	0.2	ns	7
	TSEC2_TXD[6:5] = 11 (default)			1.5		

Table 37. Local Bus General Timing Parameters—DLL Bypassed (continued)

Parameter	POR Configuration	Symbol [1]	Min	Max	Unit	Notes
Local bus clock to output high impedance for LAD/LDP	TSEC2_TXD[6:5] = 00	$t_{LBKLOZ2}$	—	0.2	ns	7
	TSEC2_TXD[6:5] = 11 (default)			1.5		

Notes:

1. The symbols used for timing specifications herein follow the pattern of $t_{\text{(First two letters of functional block)(signal)(state) (reference)(state)}}$ for inputs and $t_{\text{(First two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1). Also, t_{LBKHOX} symbolizes local bus timing (LB) for the t_{LBK} clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.
2. All timings are in reference to local bus clock for DLL bypass mode. Timings may be negative with respect to the local bus clock because the actual launch and capture of signals is done with the internal launch/capture clock, which precedes LCLK by t_{LBKHKT}.
3. Maximum possible clock skew between a clock LCLK[m] and a relative clock LCLK[n]. Skew measured between complementary signals at $OV_{DD}/2$.
4. All signals are measured from $OV_{DD}/2$ of the rising edge of local bus clock for DLL bypass mode to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
5. Input timings are measured at the pin.
6. The value of t_{LBOTOT} is defined as the sum of 1/2 or 1 ccb_clk cycle as programmed by LBCR[AHD], and the number of local bus buffer delays used as programmed at power-on reset with configuration pins TSEC2_TXD[6:5].
7. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.
8. Guaranteed by characterization.
9. Guaranteed by design.

Figure 18 provides the AC test load for the local bus.

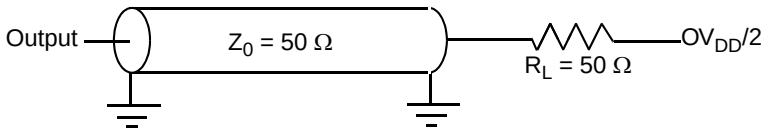

Figure 18. Local Bus AC Test Load

Figure 29 provides the test access port timing diagram.

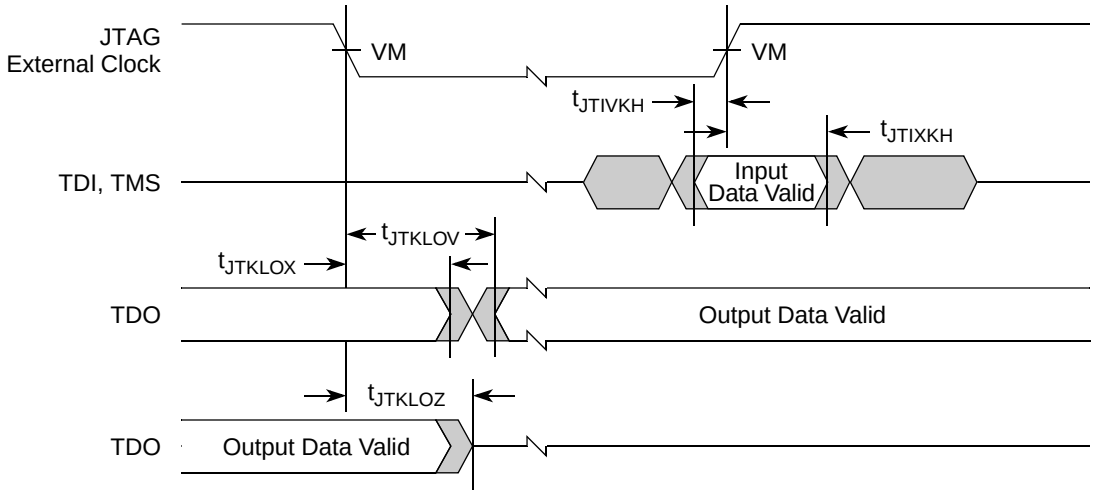

Figure 29. Test Access Port Timing Diagram

11 I²C

This section describes the DC and AC electrical characteristics for the I²C interface of the MPC8540.

11.1 I²C DC Electrical Characteristics

Table 39 provides the DC electrical characteristics for the I²C interface of the MPC8540.

Table 39. I²C DC Electrical Characteristics

At recommended operating conditions with OV_{DD} of 3.3 V ± 5%.

Parameter	Symbol	Min	Max	Unit	Notes
Input high voltage level	V_{IH}	$0.7 \times OV_{DD}$	OV_{DD}+ 0.3	V	
Input low voltage level	V_{IL}	–0.3	$0.3 \times OV_{DD}$	V	
Low level output voltage	V_{OL}	0	$0.2 \times OV_{DD}$	V	1
Pulse width of spikes which must be suppressed by the input filter	t_{I2KHKL}	0	50	ns	2
Input current each I/O pin (input voltage is between $0.1 \times OV_{DD}$ and $0.9 \times OV_{DD}$(max)	I_I	–10	10	μA	3
Capacitance for each I/O pin	C_I	—	10	pF	

Notes:

1.Output voltage (open drain or open collector) condition = 3 mA sink current.

2.Refer to the *MPC8540 Integrated Processor Preliminary Reference Manual* for information on the digital filter used.

3.I/O pins will obstruct the SDA and SCL lines if OV_{DD} is switched off.

Table 43. PCI-X AC Timing Specifications at 66 MHz (continued)

Parameter	Symbol	Min	Max	Unit	Notes
PCI-X initialization pattern to $\overline{\text{HRESET}}$ setup time	t_{PCIVRH}	10	—	clocks	11
$\overline{\text{HRESET}}$ to PCI-X initialization pattern hold time	t_{PCRHIX}	0	50	ns	6, 11

Notes:

1.See the timing measurement conditions in the *PCI-X 1.0a Specification*.

2.Minimum times are measured at the package pin (not the test point). Maximum times are measured with the test point and load circuit.

3.Setup time for point-to-point signals applies to $\overline{\text{REQ}}$ and $\overline{\text{GNT}}$ only. All other signals are bused.

4.For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

5.Setup time applies only when the device is not driving the pin. Devices cannot drive and receive signals at the same time.

6.Maximum value is also limited by delay to the first transaction (time for $\overline{\text{HRESET}}$ high to first configuration access, t_{PCRHFV}). The PCI-X initialization pattern control signals after the rising edge of $\overline{\text{HRESET}}$ must be negated no later than two clocks before the first $\overline{\text{FRAME}}$ and must be floated no later than one clock before $\overline{\text{FRAME}}$ is asserted.

7.A PCI-X device is permitted to have the minimum values shown for t_{PCKHOV} and t_{CYC} only in PCI-X mode. In conventional mode, the device must meet the requirements specified in PCI 2.2 for the appropriate clock frequency.

8.Device must meet this specification independent of how many outputs switch simultaneously.

9.The timing parameter t_{PCRHFV} is a minimum of 10 clocks rather than the minimum of 5 clocks in the *PCI-X 1.0a Specification.*

10.Guaranteed by characterization.

11.Guaranteed by design.

Table 44 provides the PCI-X AC timing specifications at 133 MHz.

Table 44. PCI-X AC Timing Specifications at 133 MHz

Parameter	Symbol	Min	Max	Unit	Notes
SYSCLK to signal valid delay	t_{PCKHOV}	—	3.8	ns	1, 2, 3, 7, 8
Output hold from SYSCLK	t_{PCKHOX}	0.7	—	ns	1, 11
SYSCLK to output high impedance	t_{PCKHOZ}	—	7	ns	1, 4, 8, 12
Input setup time to SYSCLK	t_{PCIVKH}	1.4	—	ns	3, 5, 9, 11
Input hold time from SYSCLK	t_{PCIXKH}	0.5	—	ns	11
$\overline{\text{REQ64}}$ to $\overline{\text{HRESET}}$ setup time	t_{PCRVRH}	10	—	clocks	12
$\overline{\text{HRESET}}$ to $\overline{\text{REQ64}}$ hold time	t_{PCRHRX}	0	50	ns	12
$\overline{\text{HRESET}}$ high to first $\overline{\text{FRAME}}$ assertion	t_{PCRHFV}	10	—	clocks	10, 12
PCI-X initialization pattern to $\overline{\text{HRESET}}$ setup time	t_{PCIVRH}	10	—	clocks	12

- The peak differential signal of the transmitter output or receiver input, is A – B volts.
- The peak-to-peak differential signal of the transmitter output or receiver input, is 2 × (A – B) volts.

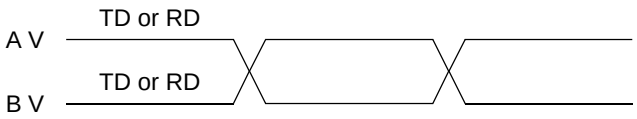

Figure 36. Differential Peak-to-Peak Voltage of Transmitter or Receiver

To illustrate these definitions using numerical values, consider the case where a LVDS transmitter has a common mode voltage of 1.2 V and each signal has a swing that goes between 1.4 and 1.0 V. Using these values, the peak-to-peak voltage swing of the signals TD, $\overline{\text{TD}}$, RD, and $\overline{\text{RD}}$ is 400 mV. The differential signal ranges between 400 and –400 mV. The peak differential signal is 400 mV, and the peak-to-peak differential signal is 800 mV.

A timing edge is the zero-crossing of a differential signal. Each skew timing parameter on a parallel bus is synchronously measured on two signals relative to each other in the same cycle, such as data to data, data to clock, or clock to clock. A skew timing parameter may be relative to the edge of a signal or to the middle of two sequential edges.

Static skew represents the timing difference between signals that does not vary over time regardless of system activity or data pattern. Path length differences are a primary source of static skew.

Dynamic skew represents the amount of timing difference between signals that is dependent on the activity of other signals and varies over time. Crosstalk between signals is a source of dynamic skew.

Eye diagrams and compliance masks are a useful way to visualize and specify driver and receiver performance. This technique is used in several serial bus specifications. An example compliance mask is shown in Figure 37. The key difference in the application of this technique for a parallel bus is that the data is source synchronous to its bus clock while serial data is referenced to its embedded clock. Eye diagrams reveal the quality (cleanness, openness, goodness) of a driver output or receiver input. An advantage of using an eye diagram and a compliance mask is that it allows specifying the quality of a signal without requiring separate specifications for effects such as rise time, duty cycle distortion, data dependent dynamic skew, random dynamic skew, etc. This allows the individual semiconductor manufacturer maximum flexibility to trade off various performance criteria while keeping the system performance constant.

In using the eye pattern and compliance mask approach, the quality of the signal is specified by the compliance mask. The mask specifies the maximum permissible magnitude of the signal and the minimum permissible eye opening. The eye diagram for the signal under test is generated according to the specification. Compliance is determined by whether the compliance mask can be positioned over the eye diagram such that the eye pattern falls entirely within the unshaded portion of the mask.

Serial specifications have clock encoded with the data, but the LP-LVDS physical layer defined by RapidIO is a source synchronous parallel port so additional specifications to include effects that are not found in serial links are required. Specifications for the effect of bit to bit timing differences caused by static skew have been added and the eye diagrams specified are measured relative to the associated clock in order to include clock to data effects. With the transmit output (or receiver input) eye diagram, the user can determine if the transmitter output (or receiver input) is compliant with an oscilloscope with the appropriate software.

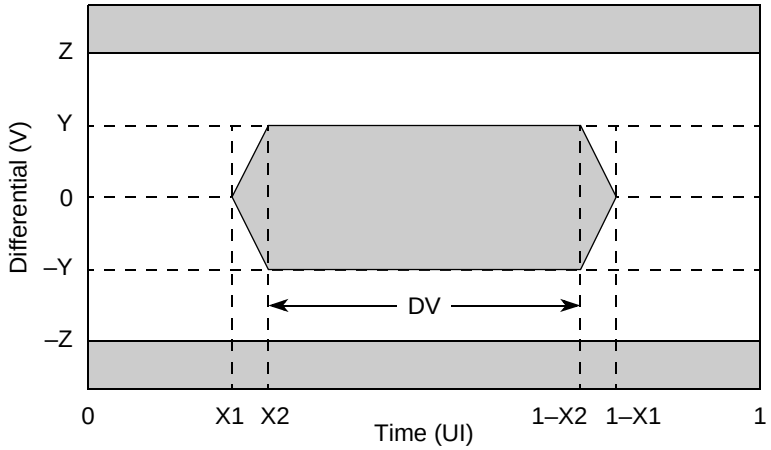

Figure 37. Example Compliance Mask

Y = minimum data valid amplitude

Z = maximum amplitude

1 UI = 1 unit interval = 1/baud rate

X1 = end of zero crossing region

X2 = beginning of data valid window

DV = data valid window = 1 – 2 × X2

The waveform of the signal under test must fall within the unshaded area of the mask to be compliant. Different masks are used for the driver output and the receiver input allowing each to be separately specified.

13.3.1 RapidIO Driver AC Timing Specifications

Driver AC timing specifications are provided in Table 47, Table 48, and Table 49. A driver shall comply with the specifications for each data rate/frequency for which operation of the driver is specified. Unless otherwise specified, these specifications are subject to the following conditions.

- The specifications apply over the supply voltage and ambient temperature ranges specified by the device vendor.
- The specifications apply for any combination of data patterns on the data signals.
- The output of a driver shall be connected to a 100 Ω, ±1%, differential (bridged) resistive load.
- Clock specifications apply only to clock signals.
- Data specifications apply only to data signals (FRAME, D[0:7]).

Table 47. RapidIO Driver AC Timing Specifications—500 Mbps Data Rate

Characteristic	Symbol	Range		Unit	Notes
		Min	Max		
Differential output high voltage	V_{OHD}	200	540	mV	1
Differential output low voltage	V_{OLD}	–540	–200	mV	1

Figure 42 shows the definitions of the data to clock static skew parameter $t_{SKEW,PAIR}$ and the data valid window parameter DV. The data and frame bits are those that are associated with the clock. The figure applies for all zero-crossings of the clock. All of the signals are differential signals. V_D represents V_{OD} for the transmitter and V_{ID} for the receiver. The center of the eye is defined as the midpoint of the region in which the magnitude of the signal voltage is greater than or equal to the minimum DV voltage.

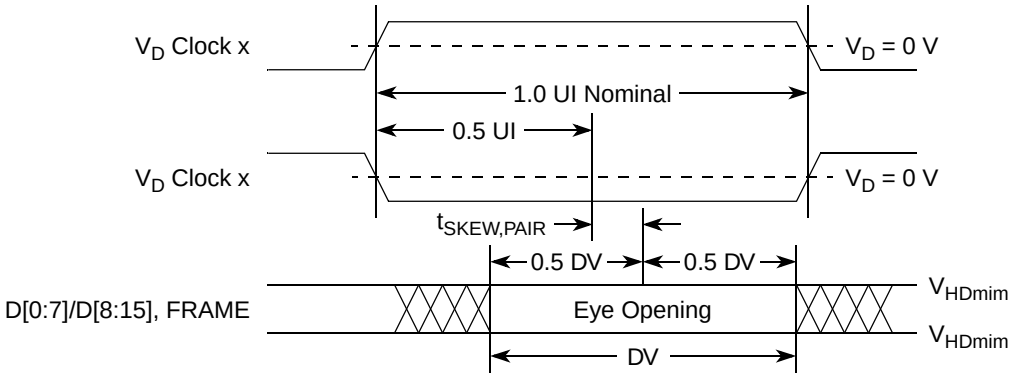

Figure 42. Data to Clock Skew

Figure 43 shows the definition of the data to data static skew parameter t_{DPAIR} and how the skew parameters are applied.

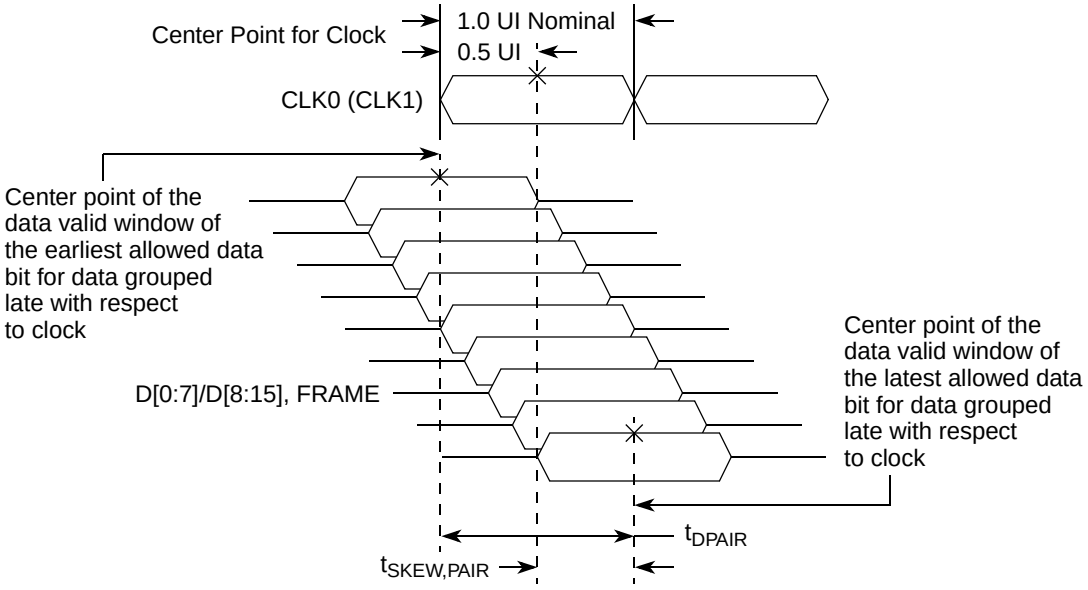

Figure 43. Static Skew Diagram

15 Clocking

This section describes the PLL configuration of the MPC8540. Note that the platform clock is identical to the CCB clock.

15.1 Clock Ranges

Table 54 provides the clocking specifications for the processor core and Table 55 provides the clocking specifications for the memory bus.

Table 54. Processor Core Clocking Specifications

Characteristic	Maximum Processor Core Frequency						Unit	Notes
	667 MHz		833 MHz		1 GHz			
	Min	Max	Min	Max	Min	Max		
e500 core processor frequency	400	667	400	833	400	1000	MHz	1, 2, 3

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 15.2, “Platform/System PLL Ratio,” and Section 15.3, “e500 Core PLL Ratio,” for ratio settings.
2.)The minimum e500 core frequency is based on the minimum platform frequency of 200 MHz.
3.)The 1.0 GHz core frequency is based on a 1.3 V VDD supply voltage.

Table 55. Memory Bus Clocking Specifications

Characteristic	Maximum Processor Core Frequency						Unit	Notes
	667 MHz		833 MHz		1 GHz			
	Min	Max	Min	Max	Min	Max		
Memory bus frequency	100	166	100	166	100	166	MHz	1, 2, 3

Notes:

1. **Caution:** The CCB to SYSCLK ratio and e500 core to CCB ratio settings must be chosen such that the resulting SYSCLK frequency, e500 (core) frequency, and CCB frequency do not exceed their respective maximum or minimum operating frequencies. Refer to Section 15.2, “Platform/System PLL Ratio,” and Section 15.3, “e500 Core PLL Ratio,” for ratio settings.
2. The memory bus speed is half of the DDR data rate, hence, half of the platform clock frequency.
3.)The 1.0 GHz core frequency is based on a 1.3 V VDD supply voltage.

15.2 Platform/System PLL Ratio

The platform clock is the clock that drives the L2 cache, the DDR SDRAM data rate, and the e500 core complex bus (CCB), and is also called the CCB clock. The values are determined by the binary value on LA[28:31] at power up, as shown in Table 56.

There is no default for this PLL ratio; these signals must be pulled to the desired values.

Table 56. CCB Clock Ratio

Binary Value of LA[28:31] Signals	Ratio Description
0000	16:1 ratio CCB clock: SYSCLK (PCI bus)
0001	Reserved
0010	2:1 ratio CCB clock: SYSCLK (PCI bus)
0011	3:1 ratio CCB clock: SYSCLK (PCI bus)
0100	4:1 ratio CCB clock: SYSCLK (PCI bus)
0101	5:1 ratio CCB clock: SYSCLK (PCI bus)
0110	6:1 ratio CCB clock: SYSCLK (PCI bus)
0111	Reserved
1000	8:1 ratio CCB clock: SYSCLK (PCI bus)
1001	9:1 ratio CCB clock: SYSCLK (PCI bus)
1010	10:1 ratio CCB clock: SYSCLK (PCI bus)
1011	Reserved
1100	12:1 ratio CCB clock: SYSCLK (PCI bus)
1101	Reserved
1110	Reserved
1111	Reserved

15.3 e500 Core PLL Ratio

Table 57 describes the clock ratio between the e500 core complex bus (CCB) and the e500 core clock. This ratio is determined by the binary value of LALE and LGPL2 at power up, as shown in Table 57.

Table 57. e500 Core to CCB Ratio

Binary Value of LALE, LGPL2 Signals	Ratio Description
00	2:1 e500 core:CCB
01	5:2 e500 core:CCB
10	3:1 e500 core:CCB
11	7:2 e500 core:CCB

Alpha Novatech 473 Sapena Ct. #15 Santa Clara, CA 95054 Internet: www.alphanovatech.com	408-749-7601
International Electronic Research Corporation (IERC) 413 North Moss St. Burbank, CA 91502 Internet: www.ctscorp.com	818-842-7277
Millennium Electronics (MEI) Loroco Sites 671 East Brokaw Road San Jose, CA 95112 Internet: www.mei-millennium.com	408-436-8770
Tyco Electronics Chip Coolers™ P.O. Box 3668 Harrisburg, PA 17105-3668 Internet: www.chipcoolers.com	800-522-6752
Wakefield Engineering 33 Bridge St. Pelham, NH 03076 Internet: www.wakefield.com	603-635-5102

Ultimately, the final selection of an appropriate heat sink depends on many factors, such as thermal performance at a given air velocity, spatial volume, mass, attachment method, assembly, and cost. Several heat sinks offered by Aavid Thermalloy, Alpha Novatech, IERC, Chip Coolers, Millennium Electronics, and Wakefield Engineering offer different heat sink-to-ambient thermal resistances, that will allow the MPC8540 to function in various environments.

16.2.1 Recommended Thermal Model

For system thermal modeling, the MPC8540 thermal model is shown in Figure 46. Five cuboids are used to represent this device. To simplify the model, the solder balls and substrate are modeled as a single block 29x29x1.47 mm with the conductivity adjusted accordingly. For modeling, the planar dimensions of the die are rounded to the nearest mm, so the die is modeled as 10x12 mm at a thickness of 0.76 mm. The bump/underfill layer is modeled as a collapsed resistance between the die and substrate assuming a conductivity of 0.6 in-plane and 1.9 W/m•K in the thickness dimension of 0.76 mm. The lid attach adhesive is also modeled as a collapsed resistance with dimensions of 10x12x0.050 mm and the conductivity of 1 W/m•K. The nickel plated copper lid is modeled as 12x14x1 mm. Note that the die and lid are not centered on the substrate; there is a 1.5 mm offset documented in the case outline drawing in Figure 44.

Conductivity	Value	Unit
Lid (12 × 14 × 1 mm)		
k_x	360	W/(m × K)
k_y	360	
k_z	360	
Lid Adhesive—Collapsed resistance (10 × 12 × 0.050 mm)		
k_x	1	
k_y	1	
k_z	1	
Die (10 × 12 × 0.76 mm)		
Bump/Underfill—Collapsed resistance (10 × 12 × 0.070 mm)		
k_x	0.6	
k_y	0.6	
k_z	1.9	
Substrate and Solder Balls (29 × 29 × 1.47 mm)		
k_x	10.2	
k_y	10.2	
k_z	1.6	

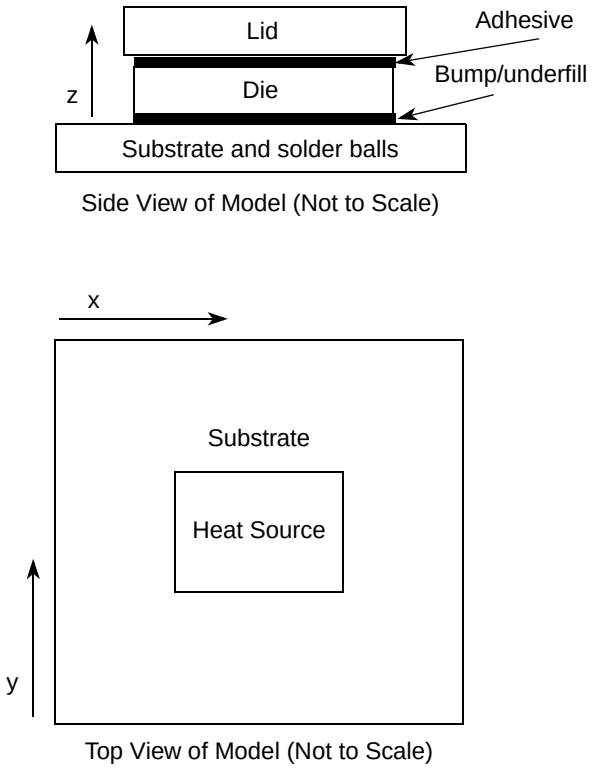

Figure 46. MPC8540 Thermal Model

16.2.2 Internal Package Conduction Resistance

For the packaging technology, shown in Table 59, the intrinsic internal conduction thermal resistance paths are as follows:

- The die junction-to-case thermal resistance
- The die junction-to-board thermal resistance

Table 61. Document Revision History (continued)

Rev. No.	Substantive Change(s)
3.0	Table 1—Corrected MII management voltage reference Section 2.1.3—New Table 2—Corrected MII management voltage reference Table 4—Added V_{DD} power table Table 5—Added AV_{DD} power table Table 7—New Table 8—New Table 9—New Table 13—Added overshoot/undershoot note. Figure 4—New Table 16—Restated $t_{MCKSKEW1}$ as $t_{MCKSKEW}$, removed $t_{MCKSKEW2}$; added speed-specific minimum values for 333, 266, and 200 MHz; updated t_{DDSHME} values. Updated chapter to reflect that GMII, MII and TBI can be run with 2.5V signalling. Table 34—Added MDIO output valid timing Table 36—Updated $t_{LBIVKH1}$, $t_{LBIXKH1}$, and t_{LBOTOT}. Table 37—New Table 20, Table 22, Table 24—Updated clock reference Table 44—Updated t_{PCIVKH} Section 14.1— Changed minimum height from 2.22 to 3.07 and maximum from 2.76 to 3.75 Table 53.—Updated MII management voltage reference and added note 20. Section 16.2.4.1—Changed θ_{JC} from 0.3 to 0.8; changed die-junction temperature from 67 to 71 Section 17.7—Added paragraph that begins “TSEC1_TXD[3:0]...”

19 Device Nomenclature

Ordering information for the parts fully covered by this specification document is provided in Section 19.1, "Nomenclature of Parts Fully Addressed by this Document."

19.1 Nomenclature of Parts Fully Addressed by this Document

Table 62 provides the Freescale part numbering nomenclature for the MPC8540. Note that the individual part numbers correspond to a maximum processor core frequency. For available frequencies, contact your local Freescale sales office. In addition to the processor frequency, the part numbering scheme also includes an application modifier which may specify special application conditions. Each part number also contains a revision code which refers to the die mask revision number.

Table 62. Part Numbering Nomenclature

MPC	nnnn	*t*	pp	ff(f)	c	r
Product Code	**Part Identifier**	**Temperature Range[1]**	**Package [2]**	**Processor Frequency [3, 4]**	**Platform Frequency**	**Revision Level**
MPC	8540	Blank = 0 to 105°C C = –40 to 105°C	PX = FC-PBGA VT = FC-PBGA (Pb-free)	833 = 833 MHz 667 = 667 MHz	L = 333 MHz J = 266 MHz	B = Rev. 2.0 (SVR = 0x80300020) C = Rev. 2.1 (SVR = 0x80300021)
MPC	8540	Blank = 0 to 105°C C = –40 to 105°C	PX = FC-PBGA VT = FC-PBGA (Pb-free)	AQ = 1.0 GHz	F = 333 MHz	B = Rev. 2.0 (SVR = 0x80300020) C = Rev. 2.1 (SVR = 0x80300021)

Notes:

1. For Temperature Range=C, Processor Frequency is limited to 667 MHz.
2. See Section 14, "Package and Pin Listings," for more information on available package types.
3. Processor core frequencies supported by parts addressed by this specification only. Not all parts described in this specification support all core frequencies. The core must be clocked at a minimum frequency of 400MHz. A device must not be used beyond the core frequency or platform frequency indicated on the device.
4. Designers should use the maximum power value corresponding to the core and platform frequency grades indicated on the device. A lower maximum power value should not be assumed for design purposes even when running at a lower frequency.